

### 1. General description

The 74LVC2G32 provides a 2-input OR gate function.

Inputs can be driven from either 3.3 V or 5 V devices. This feature allows the use of these devices as translators in a mixed 3.3 V and 5 V environment.

This device is fully specified for partial power-down applications using  $I_{OFF}$ . The  $I_{OFF}$  circuitry disables the output, preventing a damaging backflow current through the device when it is powered down.

### 2. Features and benefits

- Wide supply voltage range from 1.65 V to 5.5 V
- 5 V tolerant outputs in the Power-down mode
- High noise immunity
- $\pm 24$  mA output drive (V<sub>CC</sub> = 3.0 V)
- CMOS low power consumption
- Complies with JEDEC standard:
  - JESD8-7 (1.65 V to 1.95 V)
  - JESD8-5 (2.3 V to 2.7 V)
  - ◆ JESD8-B/JESD36 (2.7 V to 3.6 V)
- Latch-up performance exceeds 250 mA
- Direct interface with TTL levels
- Inputs accept voltages up to 5 V
- ESD protection:
  - HBM JESD22-A114F exceeds 2000 V
  - MM JESD22-A115-A exceeds 200 V
- Multiple package options
- Specified from -40 °C to +85 °C and -40 °C to +125 °C



## 3. Ordering information

Table 1. Order	ring information						
Type number	Package						
	Temperature range	Name	Description	Version			
74LVC2G32DP	–40 °C to +125 °C	TSSOP8	plastic thin shrink small outline package; 8 leads; body width 3 mm; lead length 0.5 mm	SOT505-2			
74LVC2G32DC	–40 °C to +125 °C	VSSOP8	plastic very thin shrink small outline package; 8 leads; body width 2.3 mm	SOT765-1			
74LVC2G32GT	–40 °C to +125 °C	XSON8	plastic extremely thin small outline package; no leads; 8 terminals; body 1 $\times$ 1.95 $\times$ 0.5 mm	SOT833-1			
74LVC2G32GF	–40 °C to +125 °C	XSON8	extremely thin small outline package; no leads; 8 terminals; body 1.35 $\times$ 1 $\times$ 0.5 mm	SOT1089			
74LVC2G32GD	–40 °C to +125 °C	XSON8	plastic extremely thin small outline package; no leads; 8 terminals; body $3 \times 2 \times 0.5$ mm	SOT996-2			
74LVC2G32GM	–40 °C to +125 °C	XQFN8	plastic, extremely thin quad flat package; no leads; 8 terminals; body $1.6 \times 1.6 \times 0.5$ mm	SOT902-2			
74LVC2G32GN	–40 °C to +125 °C	XSON8	extremely thin small outline package; no leads; 8 terminals; body $1.2 \times 1.0 \times 0.35$ mm	SOT1116			
74LVC2G32GS	–40 °C to +125 °C	XSON8	extremely thin small outline package; no leads; 8 terminals; body $1.35 \times 1.0 \times 0.35$ mm	SOT1203			

### 4. Marking

#### Table 2.Marking codes

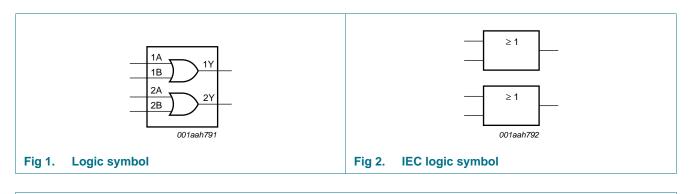
Type number	Marking code <sup>[1]</sup>
74LVC2G32DP	V32
74LVC2G32DC	V32
74LVC2G32GT	V32
74LVC2G32GF	VG
74LVC2G32GD	V32
74LVC2G32GM	V32
74LVC2G32GN	VG
74LVC2G32GS	VG

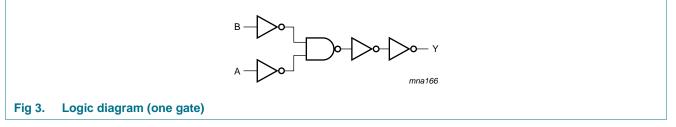
[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

74LVC2G32

**Dual 2-input OR gate** 

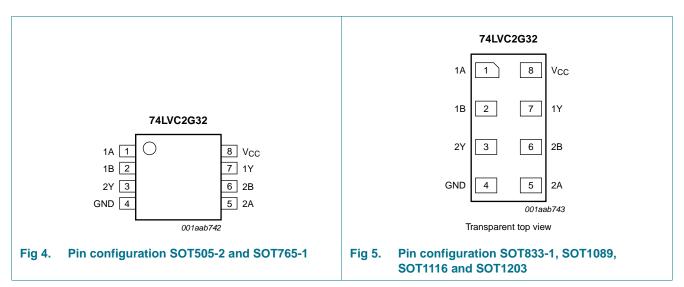
### 5. Functional diagram



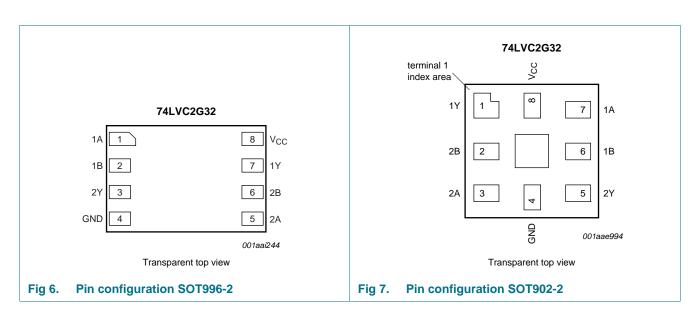


### 6. Pinning information

### 6.1 Pinning



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### 6.2 Pin description

Table 3.	Pin description				
Symbol	Pin	Pin			
	SOT505-2, SOT765-1, SOT833-1, SOT1089, SOT996-2, SOT1116 and SOT1203	SOT902-2			
1A, 2A	1, 5	7, 3	data input		
1B, 2B	2, 6	6, 2	data input		
GND	4	4	ground (0 V)		
1Y, 2Y	7, 3	1, 5	data output		
V <sub>CC</sub>	8	8	supply voltage		

## 7. Functional description

Table 4.	Function table [1]		
Input			Output
nA		nB	nY
L		L	L
L		Н	Н
Н		L	Н
Н		Н	Н

[1] H = HIGH voltage level; L = LOW voltage level.

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**Dual 2-input OR gate** 

# 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>CC</sub>	supply voltage		-0.5	+6.5	V
VI	input voltage		<u>[1]</u> –0.5	+6.5	V
Vo	output voltage	Active mode	<u>[1]</u> –0.5	V <sub>CC</sub> + 0.5	V
		Power-down mode	[2] -0.5	+6.5	V
I <sub>IK</sub>	input clamping current	V <sub>1</sub> < 0 V	-50	-	mA
Ι <sub>ΟΚ</sub>	output clamping current	$V_O < 0 V \text{ or } V_O > V_{CC}$	-	±50	mA
lo	output current	$V_{O} = 0 V$ to $V_{CC}$	-	±50	mA
I <sub>CC</sub>	supply current		-	100	mA
I <sub>GND</sub>	ground current		-100	-	mA
T <sub>stg</sub>	storage temperature		-65	+150	°C
P <sub>tot</sub>	total power dissipation	$T_{amb}$ = -40 °C to +125 °C	[3] _	300	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] When  $V_{CC}$  = 0 V (Power-down mode), the output voltage can be 5.5 V in normal condition.

[3] For TSSOP8 package: above 55 °C the value of P<sub>tot</sub> derates linearly with 2.5 mW/K.
 For VSSOP8 package: above 110 °C the value of P<sub>tot</sub> derates linearly with 8 mW/K.
 For XSON8 and XQFN8 packages: above 118 °C the value of P<sub>tot</sub> derates linearly with 7.8 mW/K.

### 9. Recommended operating conditions

Table 6.	Operating conditions				
Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>CC</sub>	supply voltage		1.65	5.5	V
VI	input voltage		0	5.5	V
Vo	output voltage	Active mode	0	V <sub>CC</sub>	V
		Power-down mode	0	5.5	V
T <sub>amb</sub>	ambient temperature		-40	+125	°C
$\Delta t / \Delta V$	input transition rise and fall rate	$V_{CC}$ = 1.65 V to 2.7 V	-	20	ns/V
		$V_{CC}$ = 2.7 V to 5.5 V	-	10	ns/V

**Dual 2-input OR gate** 

## **10. Static characteristics**

#### Table 7. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
T <sub>amb</sub> = -4	40 °C to +85 °C <u>[1]</u>					
VIH	HIGH-level input voltage	V <sub>CC</sub> = 1.65 V to 1.95 V	$0.65 \times V_{CC}$	-	-	V
		$V_{CC}$ = 2.3 V to 2.7 V	1.7	-	-	V
		$V_{CC} = 2.7 \text{ V to } 3.6 \text{ V}$	2.0	-	-	V
		$V_{CC} = 4.5 \text{ V} \text{ to } 5.5 \text{ V}$	$0.7\times V_{CC}$	-	-	V
VIL	LOW-level input voltage	V <sub>CC</sub> = 1.65 V to 1.95 V	-	-	$0.35\times V_{CC}$	V
		$V_{CC}$ = 2.3 V to 2.7 V	-	-	0.7	V
		V <sub>CC</sub> = 2.7 V to 3.6 V	-	-	0.8	V
		$V_{CC} = 4.5 \text{ V} \text{ to } 5.5 \text{ V}$	-	-	$0.3\times V_{CC}$	V
V <sub>OH</sub>	HIGH-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$				
		$I_{O}$ = -100 $\mu$ A; $V_{CC}$ = 1.65 V to 5.5 V	$V_{CC}-0.1$	-	-	V
		$I_0 = -4 \text{ mA}; V_{CC} = 1.65 \text{ V}$	1.2	1.53	-	V
		$I_0 = -8 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.9	2.13	-	V
		$I_0 = -12 \text{ mA}; V_{CC} = 2.7 \text{ V}$	2.2	2.50	-	V
		$I_0 = -24 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.3	2.60	-	V
		$I_0 = -32$ mA; $V_{CC} = 4.5$ V	3.8	4.10	-	V
V <sub>OL</sub>	LOW-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$				
		$I_{O}$ = 100 $\mu$ A; $V_{CC}$ = 1.65 V to 5.5 V	-	-	0.1	V
		I <sub>O</sub> = 4 mA; V <sub>CC</sub> = 1.65 V	-	0.08	0.45	V
		I <sub>O</sub> = 8 mA; V <sub>CC</sub> = 2.3 V	-	0.14	0.3	V
		$I_0 = 12 \text{ mA}; V_{CC} = 2.7 \text{ V}$	-	0.19	0.4	V
		I <sub>O</sub> = 24 mA; V <sub>CC</sub> = 3.0 V	-	0.37	0.55	V
		$I_0 = 32 \text{ mA}; V_{CC} = 4.5 \text{ V}$	-	0.43	0.55	V
lı	input leakage current	$V_1 = 5.5$ V or GND; $V_{CC} = 0$ V to 5.5 V	-	±0.1	±5	μΑ
I <sub>OFF</sub>	power-off leakage current	$V_1 \text{ or } V_0 = 5.5 \text{ V}; V_{CC} = 0 \text{ V}$	-	±0.1	±10	μΑ
I <sub>CC</sub>	supply current	V <sub>I</sub> = 5.5 V or GND; V <sub>CC</sub> = 1.65 V to 5.5 V; I <sub>O</sub> = 0 A	-	0.1	10	μA
Δl <sub>CC</sub>	additional supply current	per pin; $V_1 = V_{CC} - 0.6 \text{ V}$ ; $I_0 = 0 \text{ A}$ ; $V_{CC} = 2.3 \text{ V}$ to 5.5 V	-	5	500	μA
Ci	input capacitance		-	2.5	-	pF
T <sub>amb</sub> = -4	40 °C to +125 °C					
V <sub>IH</sub>	HIGH-level input voltage	V <sub>CC</sub> = 1.65 V to 1.95 V	$0.65 \times V_{CC}$	-	-	V
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	1.7	-	-	V
		$V_{CC} = 2.7 \text{ V to } 3.6 \text{ V}$	2.0	-	-	V
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	$0.7 \times V_{CC}$	-	-	V
V <sub>IL</sub>	LOW-level input voltage	$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$	-	-	$0.35 \times V_{CC}$	V
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	-	-	0.7	V
		$V_{CC} = 2.7 \text{ V to } 3.6 \text{ V}$	-	-	0.8	V
		$V_{CC} = 4.5 \text{ V to 5.5 V}$			$0.3 \times V_{CC}$	V
		$V_{CC} = 4.5 V [0 5.5 V]$	-	-	$0.3 \times vrr$	

Dual 2-input OR gate

At recom	At recommended operating conditions; voltages are referenced to GND (ground = $0 \text{ V}$ ).							
Symbol	Parameter	Conditions	Min	Тур	Max	Unit		
V <sub>OH</sub>	HIGH-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$						
		$I_{O}$ = –100 $\mu\text{A};$ $V_{CC}$ = 1.65 V to 5.5 V	$V_{CC}-0.1$	-	-	V		
		$I_0 = -4 \text{ mA}; V_{CC} = 1.65 \text{ V}$	0.95	-	-	V		
		$I_0 = -8 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.7	-	-	V		
		$I_0 = -12 \text{ mA}; V_{CC} = 2.7 \text{ V}$	1.9	-	-	V		
		$I_0 = -24 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.0	-	-	V		
		$I_0 = -32 \text{ mA}; V_{CC} = 4.5 \text{ V}$	3.4	-	-	V		
V <sub>OL</sub>	LOW-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$						
		$I_{O}$ = 100 $\mu$ A; $V_{CC}$ = 1.65 V to 5.5 V	-	-	0.1	V		
		$I_0 = 4 \text{ mA}; V_{CC} = 1.65 \text{ V}$	-	-	0.70	V		
		$I_0 = 8 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.45	V		
		$I_0 = 12 \text{ mA}; V_{CC} = 2.7 \text{ V}$	-	-	0.60	V		
		$I_0 = 24 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.80	V		
		$I_0 = 32 \text{ mA}; V_{CC} = 4.5 \text{ V}$	-	-	0.80	V		
I <sub>I</sub>	input leakage current	$V_{I}$ = 5.5 V or GND; $V_{CC}$ = 0 V to 5.5 V	-	-	±20	μA		
I <sub>OFF</sub>	power-off leakage current	$V_1$ or $V_0$ = 5.5 V; $V_{CC}$ = 0 V	-	-	±20	μA		
I <sub>CC</sub>	supply current	$V_{\rm I}$ = 5.5 V or GND; $V_{\rm CC}$ = 1.65 V to 5.5 V; $I_{\rm O}$ = 0 A	-	-	40	μΑ		
$\Delta I_{CC}$	additional supply current	per pin; V <sub>I</sub> = V <sub>CC</sub> – 0.6 V; I <sub>O</sub> = 0 A; V <sub>CC</sub> = 2.3 V to 5.5 V	-	-	5000	μΑ		

#### Table 7. Static characteristics ... continued

[1] All typical values are measured at  $T_{amb}$  = 25 °C.

### **11. Dynamic characteristics**

#### Table 8. **Dynamic characteristics**

Voltages are referenced to GND (ground 0 V); for test circuit see Figure 9.

Symbol	Parameter	Conditions	–40 °C to +85 °C		°C	–40 °C t	Unit	
			Min	Typ <mark>[1]</mark>	Мах	Min	Max	]
t <sub>pd</sub> propagation delay		nA, nB to nY; see Figure 8	<u>2]</u>					
	$V_{CC}$ = 1.65 V to 1.95 V	1.3	3.9	8.8	1.3	11	ns	
		$V_{CC}$ = 2.3 V to 2.7 V	0.8	2.4	4.7	0.8	5.9	ns
		$V_{CC} = 2.7 V$	0.8	2.7	4.8	0.8	6.0	ns
		$V_{CC}$ = 3.0 V to 3.6 V	0.9	2.2	4.2	0.9	5.3	ns
		$V_{CC}$ = 4.5 V to 5.5 V	0.7	1.7	3.2	0.7	4.0	ns

Voltages a	<i>Voltages are referenced to GND (ground 0 V); for test circuit see <u>Figure 9</u>.</i>								
Symbol	Parameter	Conditions		–40 °C to +85 °C		–40 °C to +125 °C		Unit	
				Min	Typ <mark>[1]</mark>	Max	Min	Max	
C <sub>PD</sub>	power dissipation capacitance	per gate; $V_I = GND$ to $V_{CC}$	<u>[3]</u>	-	14	-	-	-	pF

#### Table 8. Dynamic characteristics ... continued

[1] Typical values are measured at nominal V<sub>CC</sub> and at  $T_{amb} = 25$  °C.

[2]  $t_{pd}$  is the same as  $t_{PLH}$  and  $t_{PHL}$ .

[3]  $C_{PD}$  is used to determine the dynamic power dissipation ( $P_D$  in  $\mu W$ ).

 $P_{D} = C_{PD} \times V_{CC}^{2} \times f_{i} \times N + \Sigma (C_{L} \times V_{CC}^{2} \times f_{o}) \text{ where:}$ 

 $f_i$  = input frequency in MHz;

 $f_o = output frequency in MHz;$ 

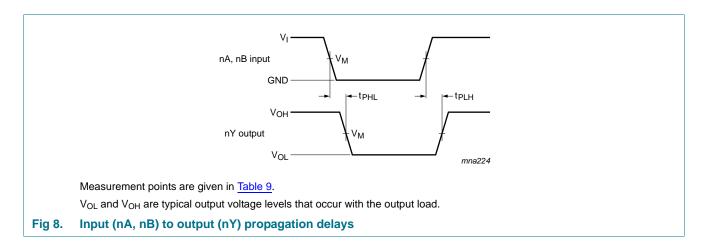
C<sub>L</sub> = output load capacitance in pF;

 $V_{CC}$  = supply voltage in V;

N = number of inputs switching;

 $\Sigma(C_L \times V_{CC}^2 \times f_o)$  = sum of outputs.

### 12. Waveforms



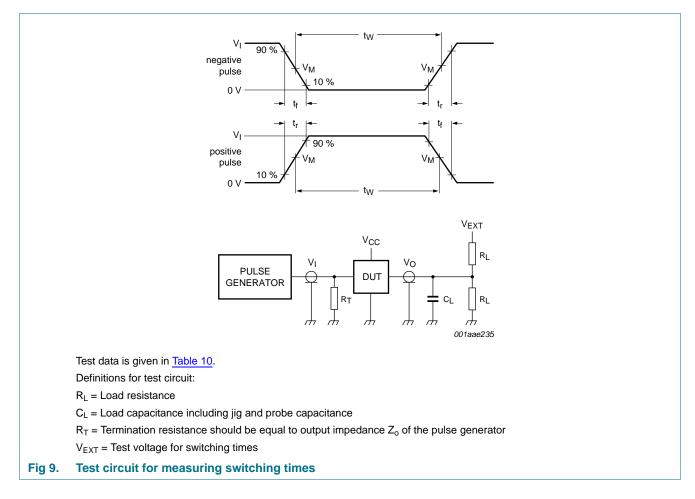
#### Table 9. **Measurement points**

Supply voltage	Input	Output
V <sub>cc</sub>	V <sub>M</sub>	V <sub>M</sub>
1.65 V to 1.95 V	0.5V <sub>CC</sub>	0.5V <sub>CC</sub>
2.3 V to 2.7 V	0.5V <sub>CC</sub>	0.5V <sub>CC</sub>
2.7 V	1.5 V	1.5 V
3.0 V to 3.6 V	1.5 V	1.5 V
4.5 V to 5.5 V	0.5V <sub>CC</sub>	0.5V <sub>CC</sub>

### **NXP Semiconductors**

# 74LVC2G32

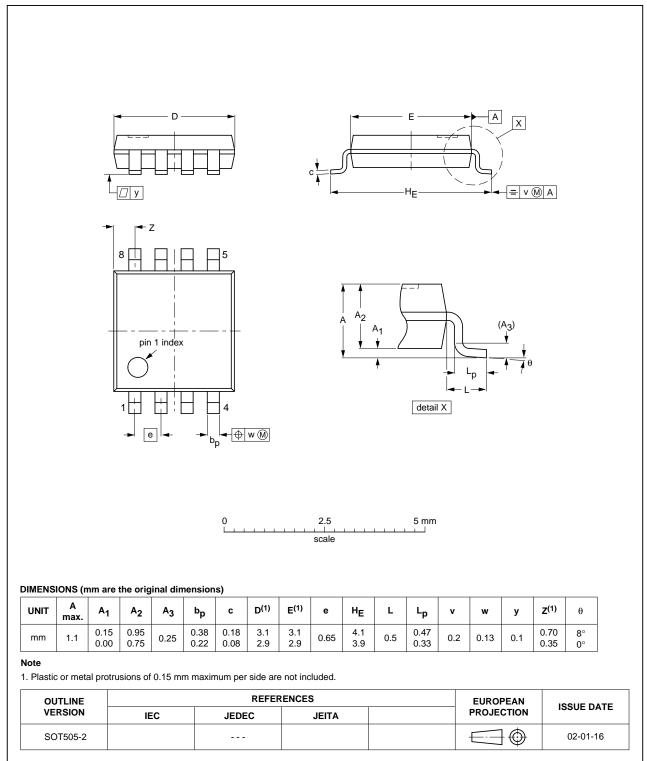
#### Dual 2-input OR gate



#### Table 10. Test data

Supply voltage	Input		Load		V <sub>EXT</sub>
V <sub>cc</sub>	VI	t <sub>r</sub> , t <sub>f</sub>	CL	RL	t <sub>PLH</sub> , t <sub>PHL</sub>
1.65 V to 1.95 V	V <sub>CC</sub>	$\leq$ 2.0 ns	30 pF	1 kΩ	open
2.3 V to 2.7 V	V <sub>CC</sub>	$\leq$ 2.0 ns	30 pF	500 Ω	open
2.7 V	2.7 V	$\leq$ 2.5 ns	50 pF	500 Ω	open
3.0 V to 3.6 V	2.7 V	$\leq$ 2.5 ns	50 pF	500 Ω	open
4.5 V to 5.5 V	V <sub>CC</sub>	$\leq$ 2.5 ns	50 pF	500 Ω	open

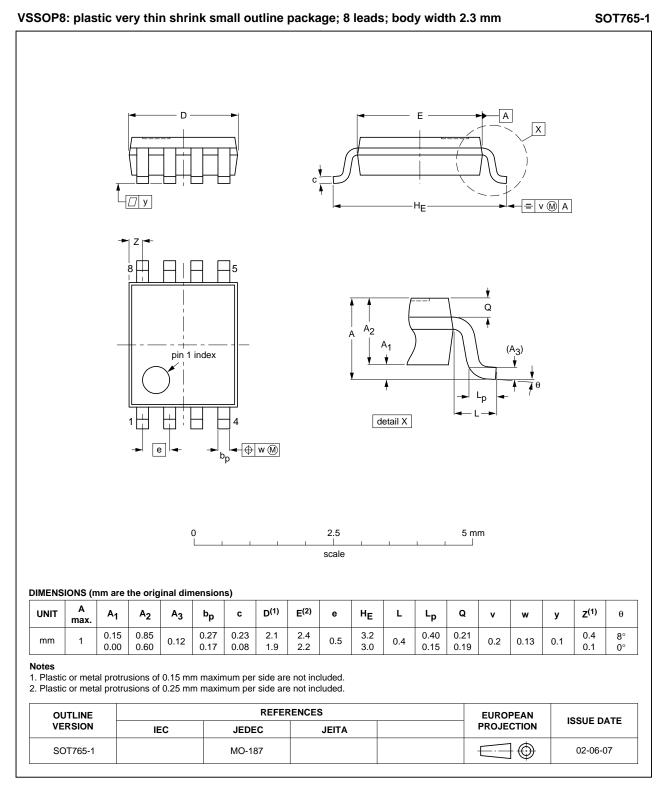
### 13. Package outline



#### TSSOP8: plastic thin shrink small outline package; 8 leads; body width 3 mm; lead length 0.5 mm SOT505-2

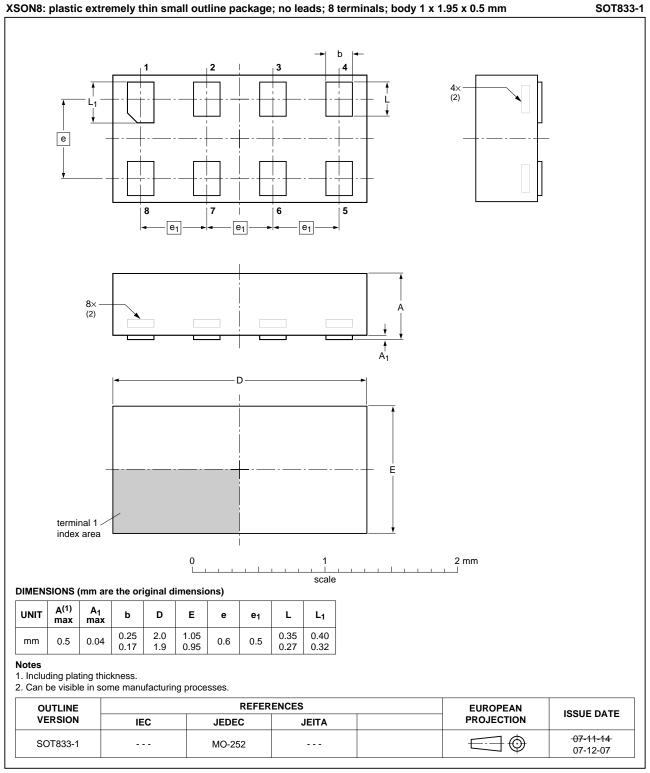
Fig 10. Package outline SOT505-2 (TSSOP8)

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#### Fig 11. Package outline SOT765-1 (VSSOP8)

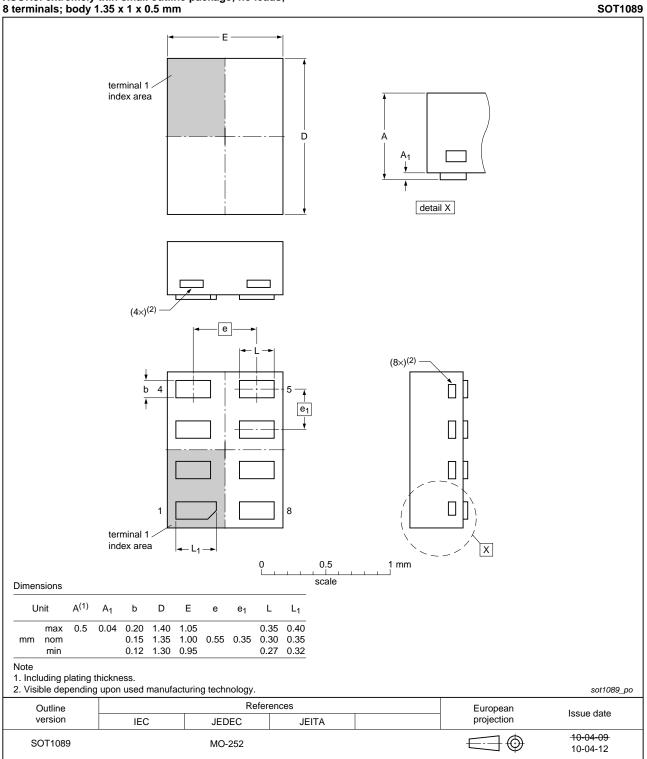
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XSON8: plastic extremely thin small outline package; no leads; 8 terminals; body 1 x 1.95 x 0.5 mm

#### Fig 12. Package outline SOT833-1 (XSON8)

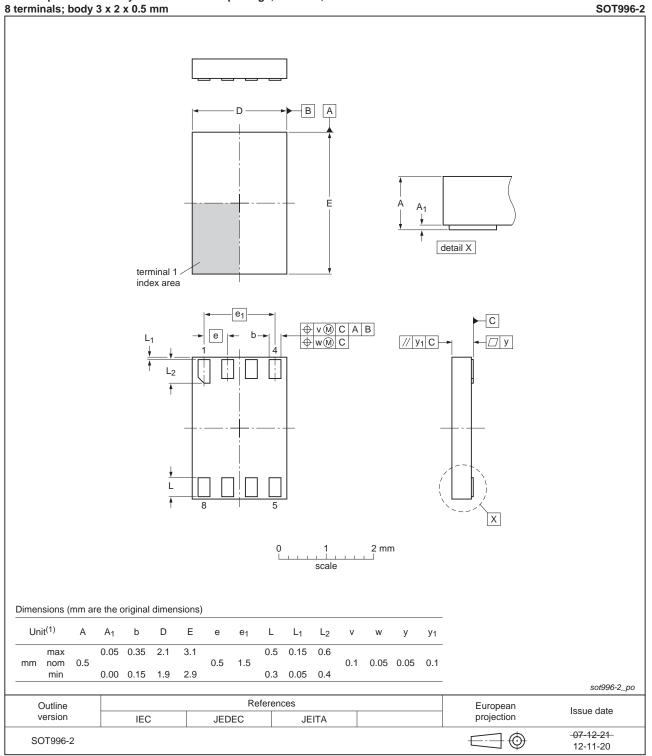
74LVC2G32 **Product data sheet** 



XSON8: extremely thin small outline package; no leads; 8 terminals; body 1.35 x 1 x 0.5 mm

#### Fig 13. Package outline SOT1089 (XSON8)

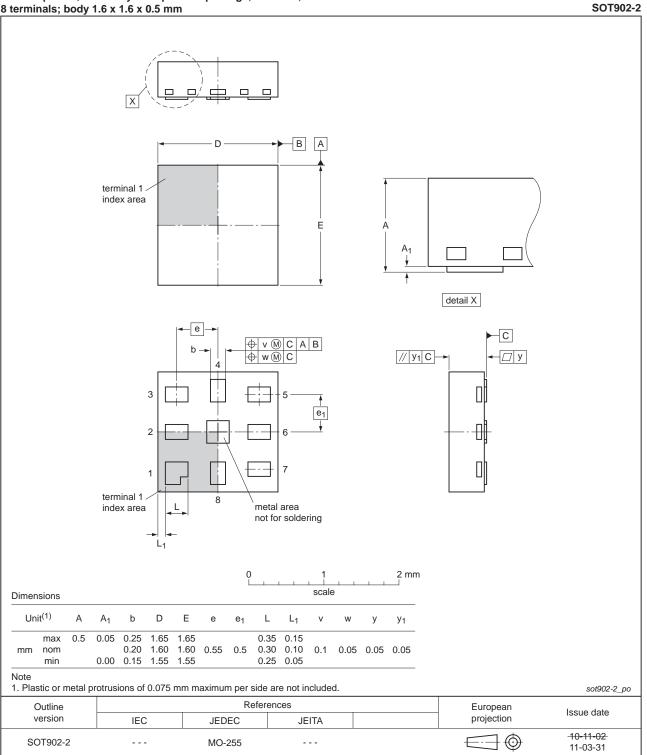
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XSON8: plastic extremely thin small outline package; no leads; 8 terminals: body 3 x 2 x 0.5 mm

Fig 14. Package outline SOT996-2 (XSON8)

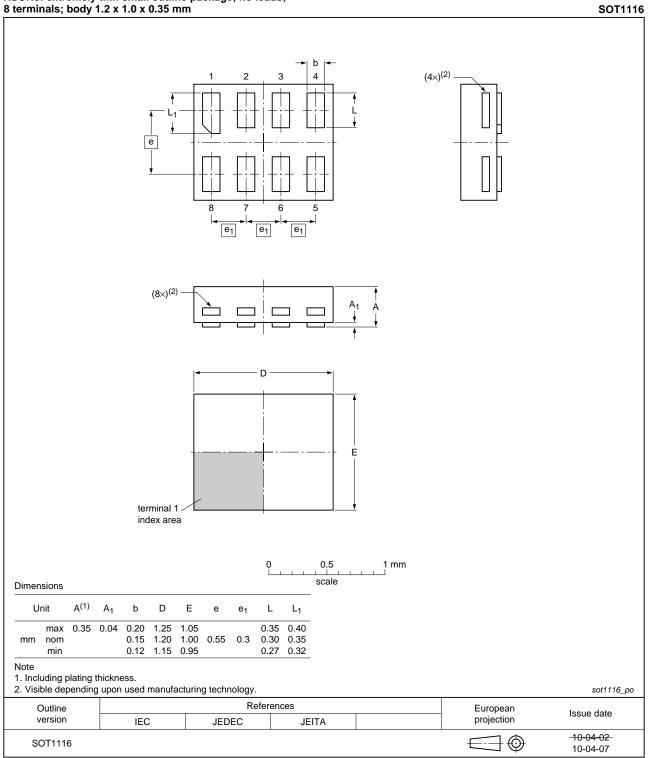
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XQFN8: plastic, extremely thin quad flat package; no leads; 8 terminals; body 1.6 x 1.6 x 0.5 mm

#### Fig 15. Package outline SOT902-2 (XQFN8)

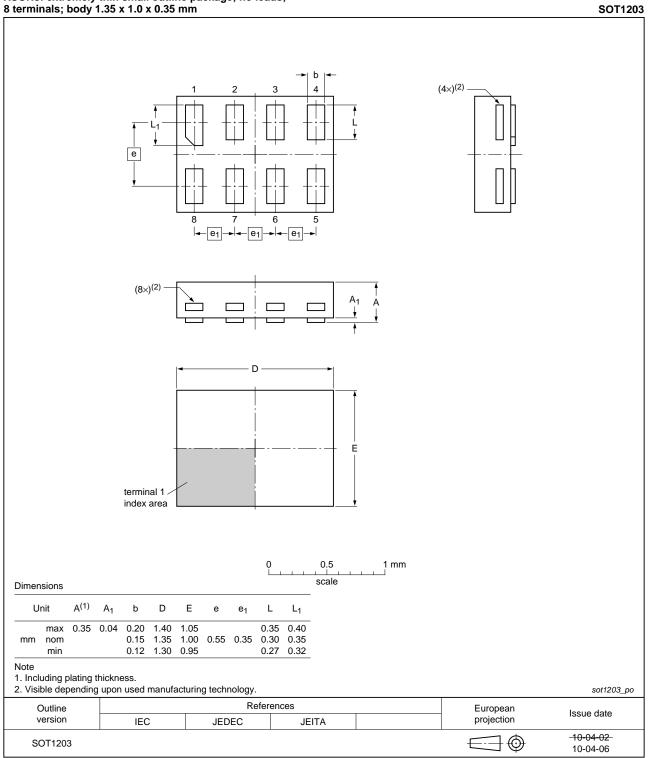
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# XSON8: extremely thin small outline package; no leads; 8 terminals; body 1.2 x 1.0 x 0.35 mm

Fig 16. Package outline SOT1116 (XSON8)

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# XSON8: extremely thin small outline package; no leads; 8 terminals; body 1.35 x 1.0 x 0.35 mm

Fig 17. Package outline SOT1203 (XSON8)

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### 14. Abbreviations

AcronymDescriptionCMOSComplementary Metal-Oxide SemiconductorDUTDevice Under TestESDElectroStatic DischargeHBMHuman Body ModelMMMachine ModelTTLTransistor-Transistor Logic	Table 11. Abbreviations				
DUTDevice Under TestESDElectroStatic DischargeHBMHuman Body ModelMMMachine Model	Acronym	Description			
ESDElectroStatic DischargeHBMHuman Body ModelMMMachine Model	CMOS	Complementary Metal-Oxide Semiconductor			
HBM     Human Body Model       MM     Machine Model	DUT	Device Under Test			
MM Machine Model	ESD	ElectroStatic Discharge			
	HBM	Human Body Model			
TTL Transistor-Transistor Logic	MM	Machine Model			
	TTL	Transistor-Transistor Logic			

## 15. Revision history

Table 12.Revision	history			
Document ID	Release date	Data sheet status	Change notice	Supersedes
74LVC2G32v.11	20130408	Product data sheet	-	74LVC2G32 v.10
Modifications:	<ul> <li>For type nu</li> </ul>	mber 74LVC2G32GD XSON	18U has changed to XS	SON8.
74LVC2G32 v.10	20120622	Product data sheet	-	74LVC2G32 v.9
Modifications:	<ul> <li>For type nu</li> </ul>	mber 74LVC2G32GM the S	OT code has changed	to SOT902-2.
74LVC2G32 v.9	20111128	Product data sheet	-	74LVC2G32 v.8
Modifications:	<ul> <li>Legal page</li> </ul>	s updated.		
74LVC2G32 v.8	20101110	Product data sheet	-	74LVC2G32 v.7
74LVC2G32 v.7	20080606	Product data sheet	-	74LVC2G32 v.6
74LVC2G32 v.6	20080227	Product data sheet	-	74LVC2G32 v.5
74LVC2G32 v.5	20070904	Product data sheet	-	74LVC2G32 v.4
74LVC2G32 v.4	20060515	Product data sheet	-	74LVC2G32 v.3
74LVC2G32 v.3	20050201	Product specification	-	74LVC2G32 v.2
74LVC2G32 v.2	20040922	Product specification	-	74LVC2G32 v.1
74LVC2G32 v.1	20031027	Product specification	-	-

### 16. Legal information

#### 16.1 Data sheet status

Document status[1][2]	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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